

Features

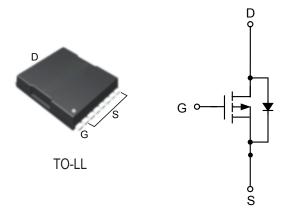
- -60V/-180A $RDS(ON)=5m\Omega(typ.)@VGS=-10V$ $RDS(ON)=6m\Omega(typ.)@VGS=-4.5V$
- 100% UIS + R_q Tested
- · Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- SMPS Synchronous Rectification
- Load Switch
- DC-DC Conversion
- Or-ing

ROHS

Pin Description



P-Channel MOSFET

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
XPX180P06LL	XPX180P06LL	TOLL	-	-	2000

Absolute Maximum Ratings (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit				
Common Ratings							
V _{DSS}	Drain-Source Voltage	-60	V				
V_{GSS}	Gate-Source Voltage	±20	v				
TJ	Maximum Junction Temperature	150	00				
T _{STG}	Storage Temperature Range	-55 to 150	- °C				
Is	Diode Continuous Forward Current	T _C =25°C	-180	А			
	Continuous Drain Current	T _C =25°C	-180				
l _D		T _C =100°C	-100	Α			
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	-400				
Ь	Maniana Barra Birainatian	T _C =25°C	395	10/			
P _D	Maximum Power Dissipation	T _C =100°C	205	- W			
R _{eJC}	Thermal Resistance-Junction to Case	Steady State	0.4	°C/W			
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	Steady State	50	°C/W			
I _{AS} b	Avalanche Current, Single pulse	L=0.5mH	-55	Α			
E _{AS} b	Avalanche Energy, Single pulse	L=0.5mH	756	mJ			

Note a: Pulse width limited by max. junction temperature.

Note b: UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature Tj=25°C).



Electrical Characteristics (T_A = 25°C unless otherwise noted)

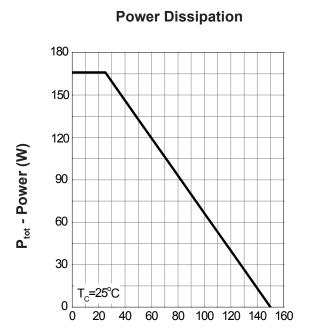
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit		
Static Ch	Static Characteristics							
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250µA	-60	-	-	V		
	Zoro Coto Voltago Drain Current	V _{DS} =-48V, V _{GS} =0V	-	-	-1	μA		
I _{DSS}	Zero Gate Voltage Drain Current	T _J =85°C	-	-	-30			
V _{GS(th)}	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{DS}=-250\mu A$	-1.0	-1.7	-2.5	V		
I _{GSS}	Gate Leakage Current	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA		
D c		V _{GS} =-10V, I _{DS} =-30A	-	5	6	mΩ		
R _{DS(ON)} c	Drain-Source On-state Resistance	V _{GS} =-4.5V, I _{DS} =-20A	-	6	8	mΩ		
	aracteristics							
V _{SD} c	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.7	-1.1	V		
t _{rr}	Reverse Recovery Time	I_{SD} =-20A, dI_{SD} /	-	29	-	ns		
Q _{rr}	Reverse Recovery Charge	dt=100A/µs	-	18	-	nC		
Dynamic	Dynamic Characteristics ^d							
R_{G}	Gate Resistance	V_{GS} =0V, V_{DS} =0V, f =1MHz	-	3.2	-	Ω		
C _{iss}	Input Capacitance	V _{GS} =0V,	-	2780	3614			
C _{oss}	Output Capacitance	V _{DS} =-20V,	-	426	-	pF		
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	-	331	-			
$t_{d(ON)}$	Turn-on Delay Time		-	13	24	ns		
t _r	Turn-on Rise Time	V_{DD} =-20V, R_{L} =20 Ω , I_{DS} =-1A, V_{GEN} =-10V,	-	11	20			
t _{d(OFF)}	Turn-off Delay Time	$R_{G}=6\Omega$	-	94	170			
t _f	Turn-off Fall Time		-	48	87			
Gate Cha	rge Characteristics ^d							
Q_g	Total Gate Charge	V _{DS} =-20V, V _{GS} =-4.5V, I _{DS} =-30A	-	32	-			
Q _g	Total Gate Charge	1/ 001/1/ 401/	-	63	88	nC		
Q_{gs}	Gate-Source Charge	V_{DS} =-20V, V_{GS} =-10V, I_{DS} =-30A	_	10.2	-			
Q_{gd}	Gate-Drain Charge	IDS OUA	-	17.3	-			

Note c : Pulse test ; pulse width≤300µs, duty cycle≤2%.

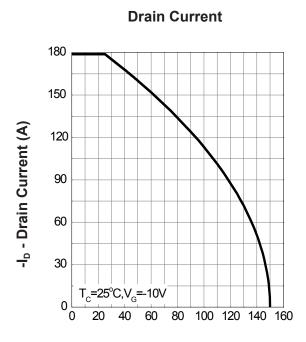
Note d: Guaranteed by design, not subject to production testing.



Typical Operating Characteristics

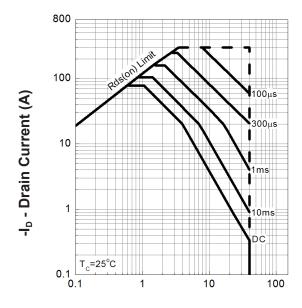


T_i - Junction Temperature (°C)



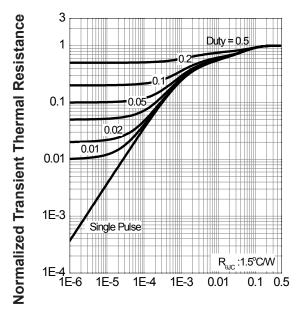
T_i - Junction Temperature (°C)

Safe Operation Area



-V_{DS} - Drain - Source Voltage (V)

Thermal Transient Impedance

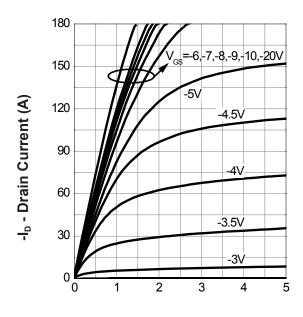


Square Wave Pulse Duration (sec)



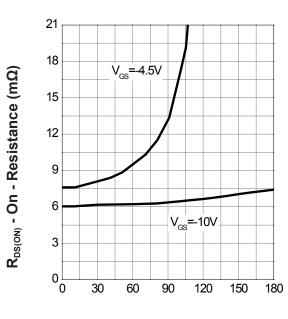
Typical Operating Characteristics(Cont.)

Output Characteristics



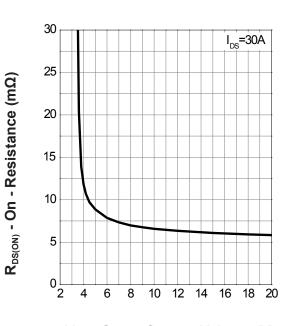
-V_{DS} - Drain - Source Voltage (V)

Drain-Source On Resistance



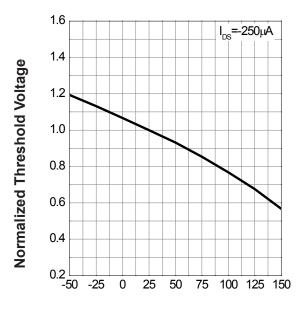
-I_D - Drain Current (A)

Gate-Source On Resistance



-V_{GS} - Gate - Source Voltage (V)

Gate Threshold Voltage

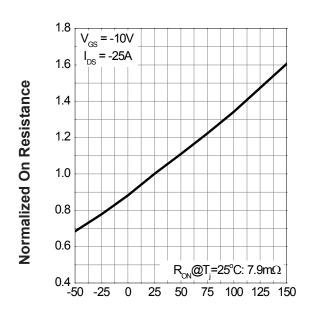


T_i - Junction Temperature (°C)



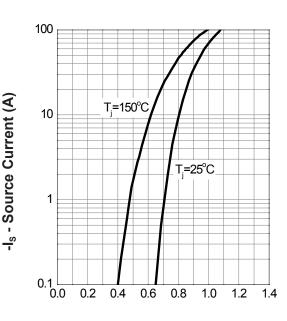
Typical Operating Characteristics(Cont.)

Drain-Source On Resistance



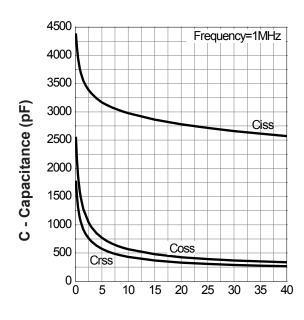
T_i - Junction Temperature (°C)

Source-Drain Diode Forward



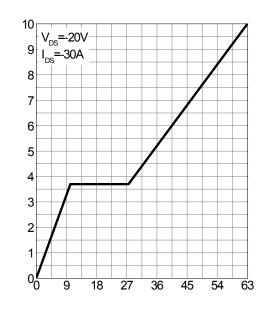
-V_{SD} - Source - Drain Voltage (V)

Capacitance



-V_{DS} - Drain-Source Voltage (V)

Gate Charge

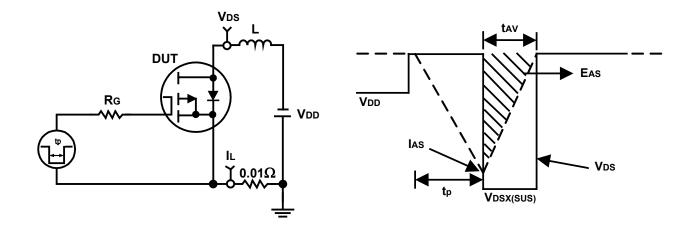


Q_G - Gate Charge (nC)

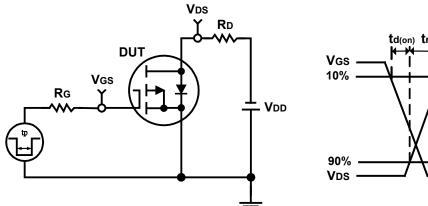
-V_{GS} - Gate-source Voltage (V)

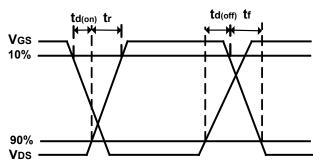


Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

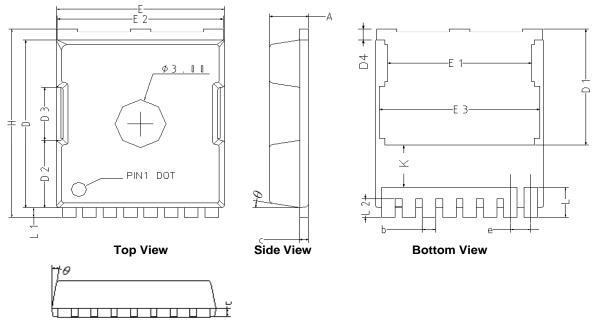






Package Information

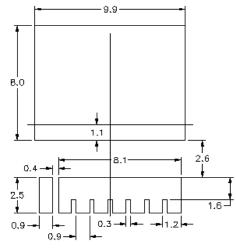
TOLL



Side View

	TO-LL				
SYMBOLS	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
Α	2.20	2.40	0.087	0.094	
b	0.70	0.90	0.028	0.035	
С	0.40	0.60	0.016	0.024	
D	10.23	10.63	0.403	0.419	
D1	7.05	7.45	0.278	0.293	
D2	3.98	4.38	0.157	0.172	
D3	3.10	3.50	0.122	0.138	
D4	0.50	0.90	0.020	0.035	
E	9.70	10.10	0.382	0.398	
E1	8.30	8.70	0.327	0.343	
E2	9.60	10.00	0.378	0.394	
E3	9.26	9.66	0.365	0.380	
H	11.53	11.93	0.454	0.470	
е	1.2 BSC		0.0472 BSC		
K	2.43	2.83	0.096	0.111	
L	1.65	2.05	0.065	0.081	
L1	0.40	0.80	0.016	0.031	
L2	0.95	1.35	0.037	0.053	
θ	6°	10°	6°	10°	

RECOMMENDED LAND PATTERN



UNIT: mm



Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245 ℃ ±5 ℃	5sec±1sec
Pb-Free device	260℃+0/-5℃	5sec±1sec



This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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